

TOSHIBA Transistor Silicon PNP Epitaxial Type

2SA2066

High-Speed Switching Applications
DC-DC Converter Applications

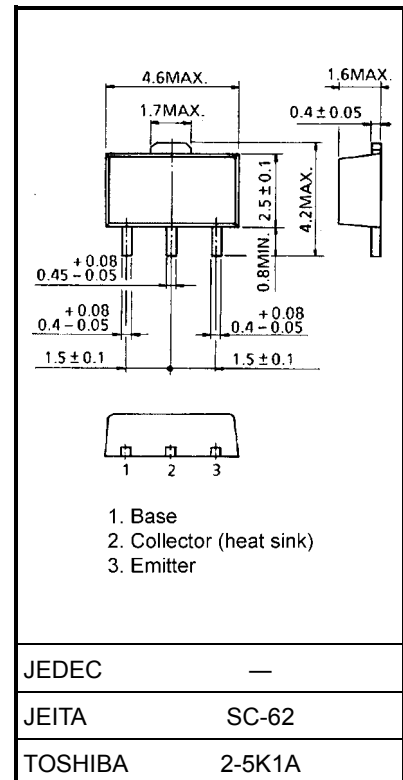
- High DC current gain: $h_{FE} = 200$ to 500 ($I_C = -0.2$ A)
- Low collector-emitter saturation voltage: $V_{CE(sat)} = -0.19$ V (max)
- High-speed switching: $t_f = 25$ ns (typ.)

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-20	V
Collector-emitter voltage	V_{CEO}	-10	V
Emitter-base voltage	V_{EBO}	-7	V
Collector current	DC	I_C	-2.0
	Pulse	I_{CP}	-3.5
Base current	I_B	-200	mA
Collector power dissipation	$t = 10$ s	P_C	2.0
	DC	(Note 1)	1.0
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to 150	$^\circ\text{C}$

Note 1: Mounted on FR4 board (glass epoxy, 1.6 mm thick, Cu area: 645 mm^2)

Unit: mm



Weight: 0.05 g (typ.)

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -20$ V, $I_E = 0$	—	—	-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -7$ V, $I_C = 0$	—	—	-0.1	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10$ mA, $I_B = 0$	-10	—	—	V
DC current gain	$h_{FE(1)}$	$V_{CE} = -2$ V, $I_C = -0.2$ A	200	—	500	
	$h_{FE(2)}$	$V_{CE} = -2$ V, $I_C = -0.6$ A	125	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -0.6$ A, $I_B = -0.02$ A	—	—	-0.19	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -0.6$ A, $I_B = -0.02$ A	—	—	-1.1	V
Switching time	Rise time	t_r	—	50	—	ns
	Storage time	t_{stg}	—	115	—	
	Fall time	t_f	—	25	—	

Marking

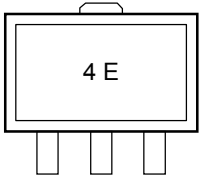
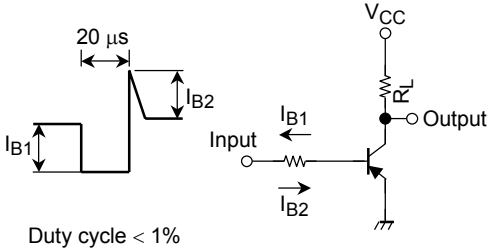
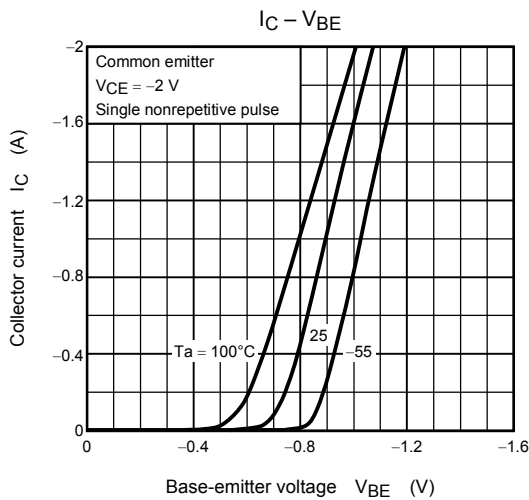
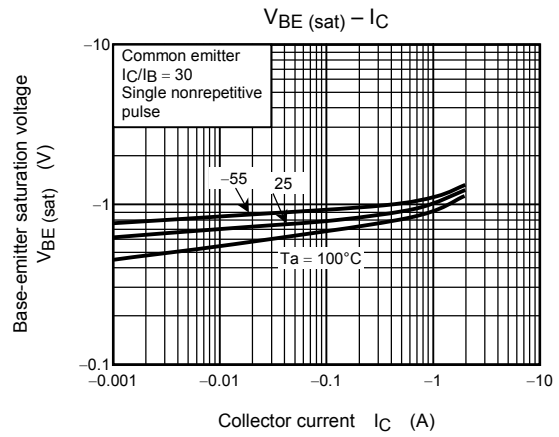
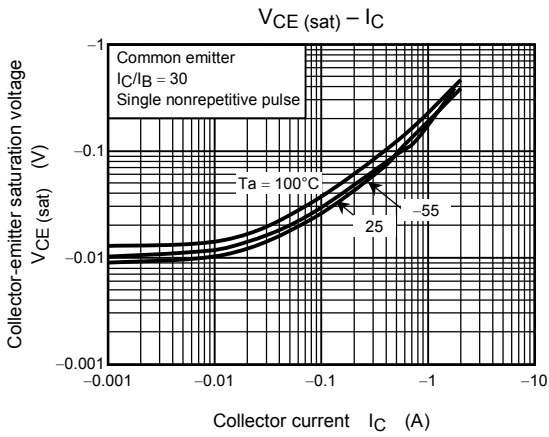
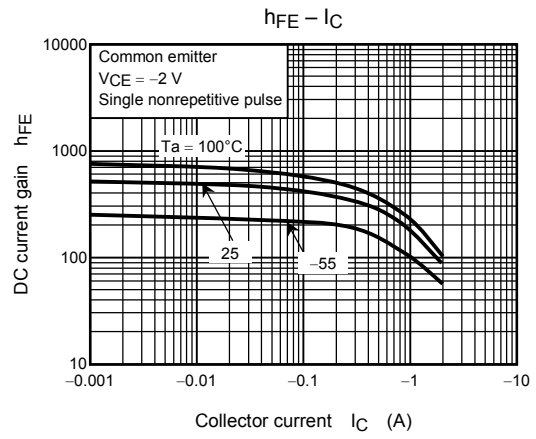
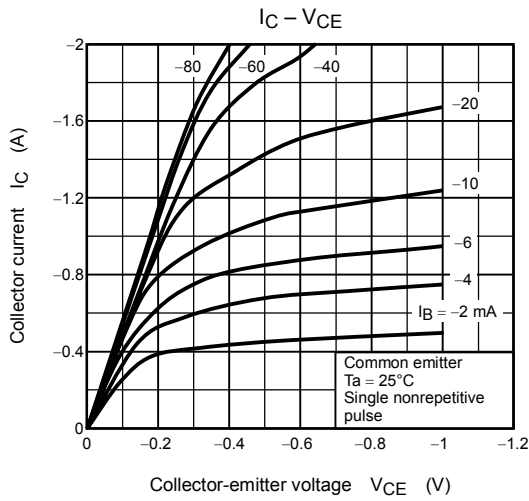
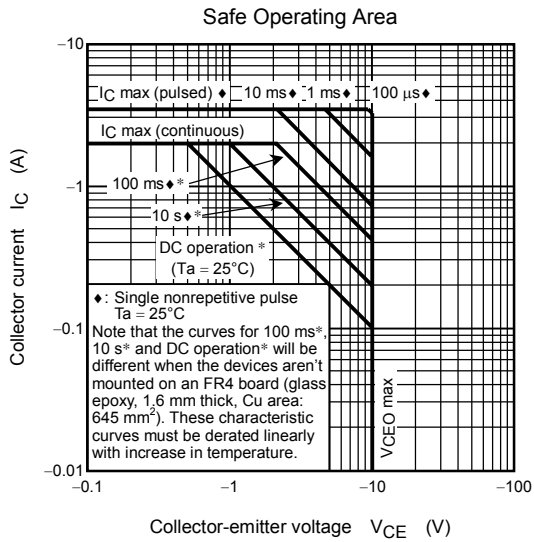
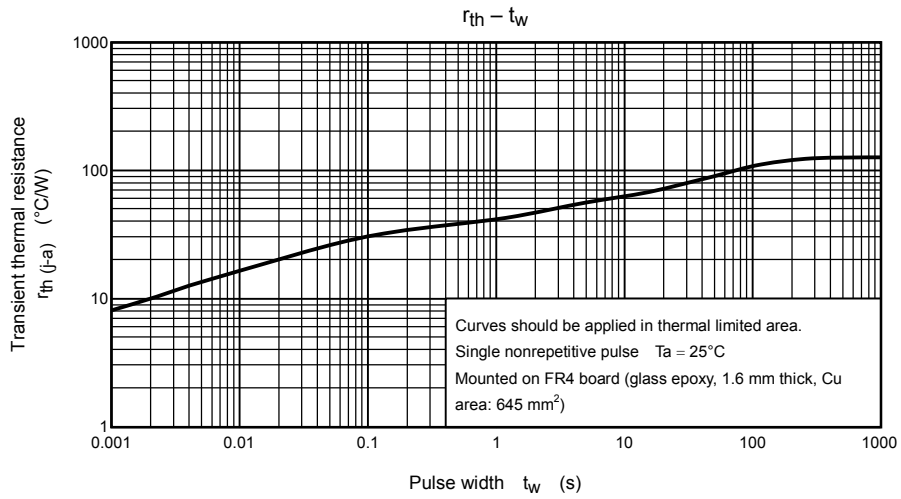


Figure 1 Switching Time Test Circuit & Timing Chart





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